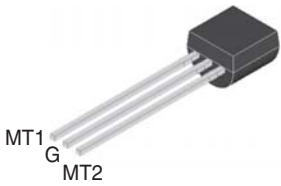
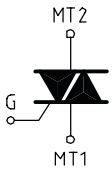


## LOGIC LEVEL TRIAC

<p style="text-align: center;"><b>TO92</b> (Plastic)</p>  	<table style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 50%; text-align: center;"><b>On-State Current</b> 1 Amp</td> <td style="width: 50%; text-align: center;"><b>Gate Trigger Current</b> &lt; 10 mA</td> </tr> <tr> <td colspan="2" style="text-align: center; padding: 10px 0;"><b>Off-State Voltage</b> 200 V ÷ 600 V</td> </tr> </table> <p style="margin-top: 20px;">This series of <b>TRIACs</b> uses a high performance PNPN technology.</p> <p>These parts are intended for general purpose AC switching applications with highly inductive loads.</p>	<b>On-State Current</b> 1 Amp	<b>Gate Trigger Current</b> < 10 mA	<b>Off-State Voltage</b> 200 V ÷ 600 V	
<b>On-State Current</b> 1 Amp	<b>Gate Trigger Current</b> < 10 mA				
<b>Off-State Voltage</b> 200 V ÷ 600 V					

### Absolute Maximum Ratings, according to IEC publication No. 134

SYMBOL	PARAMETER	CONDITIONS	Value	Unit
$I_{T(RMS)}$	RMS On-state Current (full sine wave)	All Conduction Angle, $T_c = 95\text{ }^\circ\text{C}$	1	A
$I_{TSM}$	Non-repetitive On-State Current	Full Cycle, 60 Hz ( $t = 16.7\text{ ms}$ )	8.5	A
$I_{TSM}$	Non-repetitive On-State Current	Full Cycle, 50 Hz ( $t = 20\text{ ms}$ )	8	A
$I^2t$	Fusing Current	$t_p = 10\text{ms}$ , Half Cycle	0.32	$\text{A}^2\text{s}$
$I_{GM}$	Peak Gate Current	$20\text{ }\mu\text{s}$ max. $T_j = 125\text{ }^\circ\text{C}$	1	A
$P_{G(AV)}$	Average Gate Power Dissipation	$T_j = 125\text{ }^\circ\text{C}$	0.1	W
$di/dt$	Critical rate of rise of On-State current	$I_G = 2 \times I_{GT}$ , $t_r \leq 100\text{ns}$ $f = 120\text{ Hz}$ , $T_j = 125\text{ }^\circ\text{C}$	20	A/ $\mu\text{s}$
$T_j$	Operating Temperature		(-40 + 125)	$^\circ\text{C}$
$T_{stg}$	Storage Temperature		(-40 + 150)	$^\circ\text{C}$
$T_{sld}$	Soldering Temperature	10s max.	260	$^\circ\text{C}$

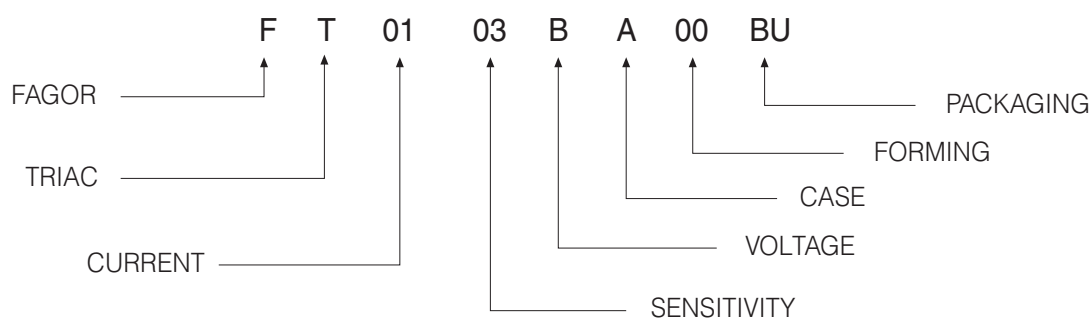
SYMBOL	PARAMETER	VOLTAGE			Unit
		B	D	M	
$V_{DRM}$	Repetitive Peak Off State	200	400	600	V
$V_{RRM}$	Voltage				

**LOGIC LEVEL TRIAC**
**Electrical Characteristics**

SYMBOL	PARAMETER	CONDITIONS	Quadrant		SENSITIVITY				Unit
					03	05	07	09	
I <sub>GT</sub> <sup>(1)</sup>	Gate Trigger Current	V <sub>D</sub> = 12 V <sub>DC</sub> , R <sub>L</sub> = 33Ω, T <sub>j</sub> = 25 °C	Q1÷Q3	MAX	3	5	5	10	mA
			Q4	MAX	5	5	7	10	mA
V <sub>GT</sub>	Gate Trigger Voltage	V <sub>D</sub> = 12 V <sub>DC</sub> , R <sub>L</sub> = 33Ω, T <sub>j</sub> = 25 °C	Q1÷Q3	MAX	1.3				V
			Q1÷Q4	MAX	1.3				V
V <sub>GD</sub>	Gate Non Trigger Voltage	V <sub>D</sub> = V <sub>DRM</sub> , R <sub>L</sub> = 3.3kΩ, T <sub>j</sub> = 125 °C	Q1÷Q3	MIN	0.2				V
			Q1÷Q4	MIN	0.2				V
I <sub>H</sub> <sup>(2)</sup>	Holding Current	I <sub>T</sub> = 100 mA, Gate open, T <sub>j</sub> = 25 °C		MAX	7	10	10	20	mA
I <sub>L</sub>	Latching Current	I <sub>G</sub> = 1.2 I <sub>GT</sub> , T <sub>j</sub> = 25 °C	Q1,Q3	MAX	7	10	10	20	mA
			Q1,Q3,Q4	MAX					mA
			Q2	MAX					15
dV/dt <sup>(2)</sup>	Critical Rate of Voltage Rise	V <sub>D</sub> = 0.67 x V <sub>DRM</sub> , Gate open T <sub>j</sub> = 125 °C		MIN	10	20	20	50	V/μs
(dI/dt) <sub>c</sub> <sup>(2)</sup>	Critical Rate of Current Rise	(dv/dt) <sub>c</sub> = 0.1 V/μs T <sub>j</sub> = 125 °C (dv/dt) <sub>c</sub> = 10 V/μs T <sub>j</sub> = 125 °C without snubber T <sub>j</sub> = 125 °C		MIN	1.2	1.8	1.8	2.5	A/ms
				MIN	0.6	0.9	0.9	1.5	A/ms
				MIN					
V <sub>TM</sub> <sup>(2)</sup>	On-state Voltage	I <sub>T</sub> = 1.1 Amp, tp = 380 μs, T <sub>j</sub> = 25 °C		MAX	1.5				V
V <sub>t(O)</sub> <sup>(2)</sup>	Threshold Voltage	T <sub>j</sub> = 125 °C		MAX	0.95				V
r <sub>d</sub> <sup>(2)</sup>	Dynamic resistance	T <sub>j</sub> = 125 °C		MAX	1000				mΩ
I <sub>DRM</sub> /I <sub>RRM</sub>	Off-State Leakage Current	V <sub>D</sub> = V <sub>DRM</sub> , T <sub>j</sub> = 125 °C		MAX	0.5				mA
		V <sub>R</sub> = V <sub>RRM</sub> , T <sub>j</sub> = 25 °C		MAX	5				μA
R <sub>th(j-c)</sub>	Thermal Resistance Junction-Case	for AC 360° conduction angle			80				°C/W
R <sub>th(j-a)</sub>	Thermal Resistance Junction-Ambient	S = 1cm <sup>2</sup>			150				°C/W

(1) Minimum I<sub>GT</sub> is guaranteed at 5% of I<sub>GT</sub> max.

(2) For either polarity of electrode MT2 voltage with reference to electrode MT1.

**PART NUMBER INFORMATION**


**LOGIC LEVEL TRIAC**

Fig. 1: Maximum power dissipation versus RMS on-state current (full cycle)

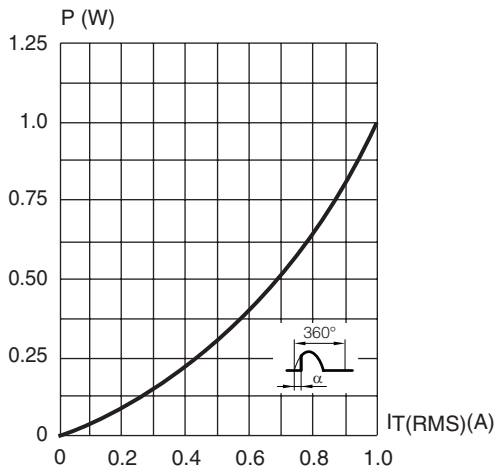


Fig. 2: RMS on-state current versus case temperature (full cycle).

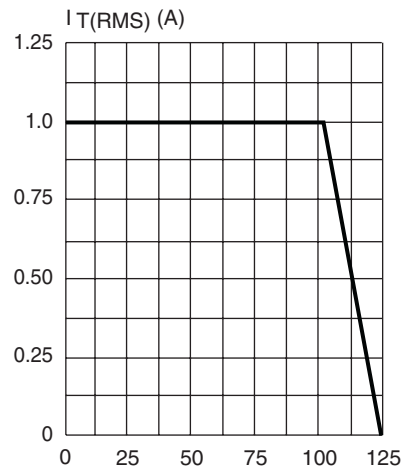


Fig. 3: Relative variation of thermal impedance versus pulse duration.

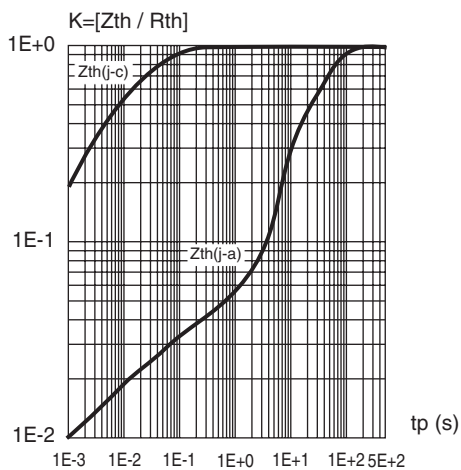


Fig. 4: On-state characteristics (maximum values)

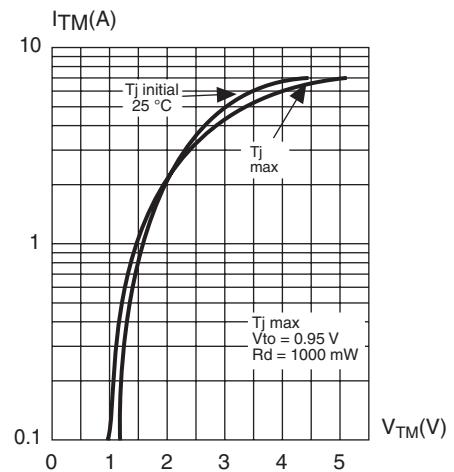


Fig. 5: Surge peak on-state current versus number of cycles

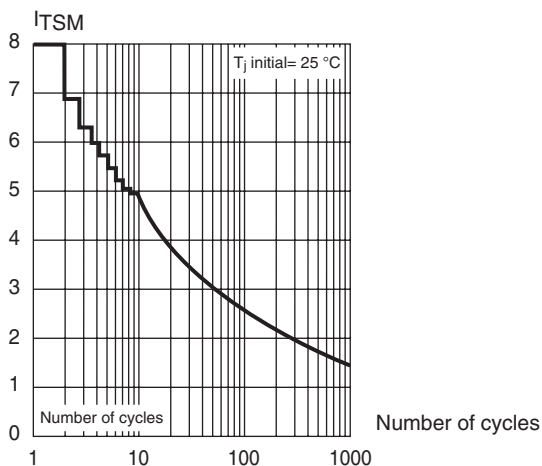
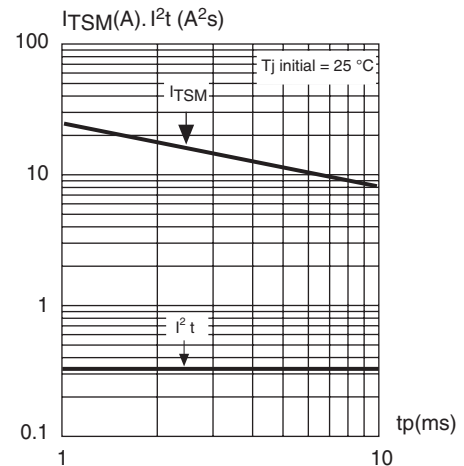


Fig. 6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10$ ms, and corresponding value of  $I^2 t$ .



### LOGIC LEVEL TRIAC

Fig. 7: Relative variation of gate trigger current, holding current and latching versus junction temperature (typical values)

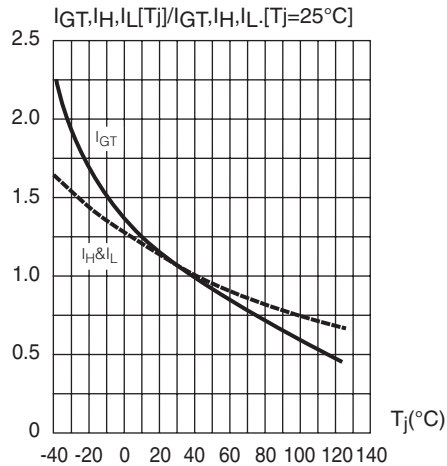


Fig. 8: Relative variation of critical rate of decrease of main current versus junction temperature

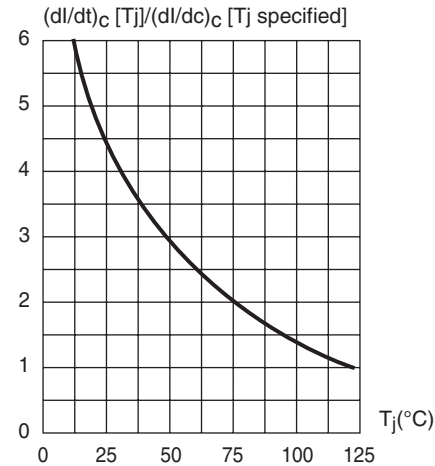
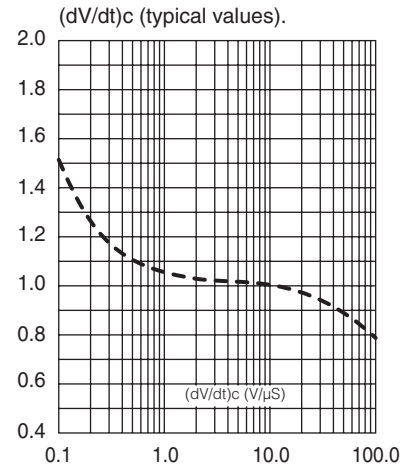


Fig. 9: Relative variation of critical rate of decrease of main current versus



#### PACKAGE MECHANICAL DATA

TO92

REF.	DIMENSIONS		
	Millimeters		
	Min.	Typ.	Max.
A	0.90	1.20	1.50
B	4.40	4.60	4.80
C	2.34	2.54	2.74
D	1.07	1.27	1.47
E	4.40	4.60	4.80
F	12.70	14.10	15.50
G	3.40	3.60	3.86
H	1.30	1.50	1.70
a	0.38	0.44	0.51
b	0.33	0.41	0.51

Marking: type number  
Weight: 0.2 g

#### PACKAGE MECHANICAL DATA

TO92 (FOR TAPE & REEL)

REF.	DIMENSIONS		
	Millimeters		
	Min.	Typ.	Max.
A	0.90	1.20	1.50
B	4.40	4.60	4.80
C	4.96	5.08	5.20
D	2.42	2.54	2.66
E	4.40	4.60	4.80
F	12.70	14.10	15.50
G	3.40	3.60	3.86
a	0.38	0.44	0.51
b	0.33	0.41	0.51

Marking: type number  
Weight: 0.2 g